

BZV55 series

Voltage regulator diodes

Rev. 04 — 19 July 2007

Product data sheet

1. Product profile

1.1 General description

Low-power voltage regulator diodes in small hermetically sealed glass SOD80C Surface-Mounted Device (SMD) packages. The diodes are available in the normalized E24 $\pm 2\%$ (BZV55-B) and approximately $\pm 5\%$ (BZV55-C) tolerance range. The series consists of 37 types with nominal working voltages from 2.4 V to 75 V.

1.2 Features

- Non-repetitive peak reverse power dissipation: ≤ 40 W
- Total power dissipation: ≤ 500 mW
- Two tolerance series: $\pm 2\%$ and $\pm 5\%$
- Wide working voltage range: nominal 2.4 V to 75 V (E24 range)
- Low differential resistance
- Small hermetically sealed glass SMD package

1.3 Applications

- General regulation functions

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 10$ mA	-	-	0.9	V
P_{ZSM}	non-repetitive peak reverse power dissipation		[1]	-	40	W

[1] $t_p = 100$ μ s; square wave; $T_j = 25$ °C prior to surge

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	
2	anode		

006aaa152

[1] The marking band indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BZV55-B2V4 to BZV55-C75 ^[1]	-	hermetically sealed glass surface-mounted package; 2 connectors	SOD80C

[1] The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BZV55-B2V4 to BZV55-C75	marking band

[1] blue: made in China
yellow: made in Philippines

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_F	forward current		-	250	mA
I_{ZSM}	non-repetitive peak reverse current		^[1] -	see Table 8 and 9	
P_{ZSM}	non-repetitive peak reverse power dissipation		^[1] -	40	W
P_{tot}	total power dissipation	$T_{amb} \leq 50\text{ °C}$	^[2] -	400	mW
		$T_{tp} \leq 50\text{ °C}$	^[2] -	500	mW
T_{stg}	storage temperature		-65	+200	°C
T_j	junction temperature		-65	+200	°C

[1] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ °C}$ prior to surge

[2] Device mounted on a ceramic substrate of $10 \times 10 \times 0.6\text{ mm}$.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	^[1] -	-	380	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	300	K/W

[1] Device mounted on a ceramic substrate of $10 \times 10 \times 0.6\text{ mm}$.

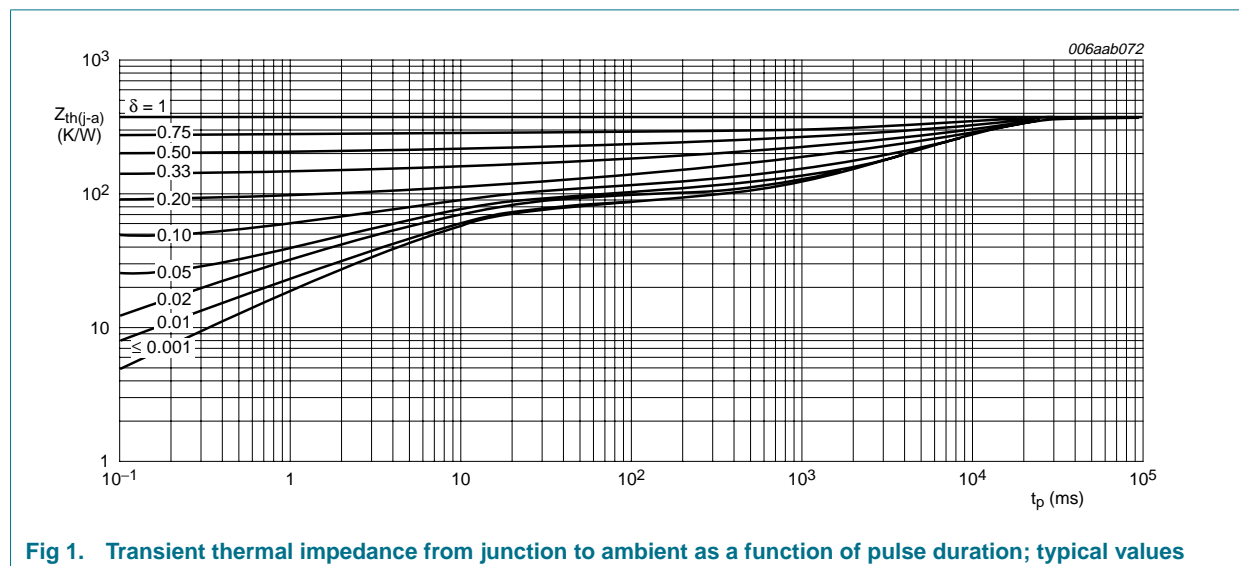


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _F	forward voltage	I _F = 10 mA	-	-	0.9	V
I _R	reverse current					
	BZV55-B/C2V4	V _R = 1 V	-	-	50	μA
	BZV55-B/C2V7	V _R = 1 V	-	-	20	μA
	BZV55-B/C3V0	V _R = 1 V	-	-	10	μA
	BZV55-B/C3V3	V _R = 1 V	-	-	5	μA
	BZV55-B/C3V6	V _R = 1 V	-	-	5	μA
	BZV55-B/C3V9	V _R = 1 V	-	-	3	μA
	BZV55-B/C4V3	V _R = 1 V	-	-	3	μA
	BZV55-B/C4V7	V _R = 2 V	-	-	3	μA
	BZV55-B/C5V1	V _R = 2 V	-	-	2	μA
	BZV55-B/C5V6	V _R = 2 V	-	-	1	μA
	BZV55-B/C6V2	V _R = 4 V	-	-	3	μA
	BZV55-B/C6V8	V _R = 4 V	-	-	2	μA
	BZV55-B/C7V5	V _R = 5 V	-	-	1	μA
	BZV55-B/C8V2	V _R = 5 V	-	-	700	nA
	BZV55-B/C9V1	V _R = 6 V	-	-	500	nA
	BZV55-B/C10	V _R = 7 V	-	-	200	nA
	BZV55-B/C11	V _R = 8 V	-	-	100	nA
	BZV55-B/C12	V _R = 8 V	-	-	100	nA
	BZV55-B/C13	V _R = 8 V	-	-	100	nA
	BZV55-B/C15 to BZV55-B/C75	V _R = 0.7V _{Z(nom)}	-	-	50	nA

Table 8. Characteristics per type; BZV55-B2V4 to BZV55-C24

 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

BZV55-xx	Sel	Working voltage V_Z (V)		Differential resistance r_{dif} (Ω)				Temperature coefficient S_Z (mV/K)			Diode capacitance C_d (pF) ^[1]	Non-repetitive peak reverse current I_{ZSM} (A) ^[2]
				$I_Z = 1\text{ mA}$		$I_Z = 5\text{ mA}$		$I_Z = 5\text{ mA}$				
		Min	Max	Typ	Max	Typ	Max	Min	Typ	Max	Max	Max
2V4	B	2.35	2.45	275	600	70	100	-3.5	-1.6	0	450	6.0
	C	2.2	2.6									
2V7	B	2.65	2.75	300	600	75	100	-3.5	-2.0	0	450	6.0
	C	2.5	2.9									
3V0	B	2.94	3.06	325	600	80	95	-3.5	-2.1	0	450	6.0
	C	2.8	3.2									
3V3	B	3.23	3.37	350	600	85	95	-3.5	-2.4	0	450	6.0
	C	3.1	3.5									
3V6	B	3.53	3.67	375	600	85	90	-3.5	-2.4	0	450	6.0
	C	3.4	3.8									
3V9	B	3.82	3.98	400	600	85	90	-3.5	-2.5	0	450	6.0
	C	3.7	4.1									
4V3	B	4.21	4.39	410	600	80	90	-3.5	-2.5	0	450	6.0
	C	4.0	4.6									
4V7	B	4.61	4.79	425	500	50	80	-3.5	-1.4	0.2	300	6.0
	C	4.4	5.0									
5V1	B	5.0	5.2	400	480	40	60	-2.7	-0.8	1.2	300	6.0
	C	4.8	5.4									
5V6	B	5.49	5.71	80	400	15	40	-2.0	1.2	2.5	300	6.0
	C	5.2	6.0									
6V2	B	6.08	6.32	40	150	6	10	0.4	2.3	3.7	200	6.0
	C	5.8	6.6									
6V8	B	6.66	6.94	30	80	6	15	1.2	3.0	4.5	200	6.0
	C	6.4	7.2									
7V5	B	7.35	7.65	30	80	6	15	2.5	4.0	5.3	150	4.0
	C	7.0	7.9									
8V2	B	8.04	8.36	40	80	6	15	3.2	4.6	6.2	150	4.0
	C	7.7	8.7									
9V1	B	8.92	9.28	40	100	6	15	3.8	5.5	7.0	150	3.0
	C	8.5	9.6									
10	B	9.8	10.2	50	150	8	20	4.5	6.4	8.0	90	3.0
	C	9.4	10.6									
11	B	10.8	11.2	50	150	10	20	5.4	7.4	9.0	85	2.5
	C	10.4	11.6									
12	B	11.8	12.2	50	150	10	25	6.0	8.4	10.0	85	2.5
	C	11.4	12.7									

Table 8. Characteristics per type; BZV55-B2V4 to BZV55-C24 ...continued

 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

BZV55-x xx	Sel	Working voltage V_Z (V)		Differential resistance r_{dif} (Ω)				Temperature coefficient S_Z (mV/K)			Diode capacitance C_d (pF) ^[1]	Non-repetitive peak reverse current I_{ZSM} (A) ^[2]
				$I_Z = 1\text{ mA}$		$I_Z = 5\text{ mA}$		$I_Z = 5\text{ mA}$				
		Min	Max	Typ	Max	Typ	Max	Min	Typ	Max	Max	Max
13	B	12.7	13.3	50	170	10	30	7.0	9.4	11.0	80	2.5
	C	12.4	14.1									
15	B	14.7	15.3	50	200	10	30	9.2	11.4	13.0	75	2.0
	C	13.8	15.6									
16	B	15.7	16.3	50	200	10	40	10.4	12.4	14.0	75	1.5
	C	15.3	17.1									
18	B	17.6	18.4	50	225	10	45	12.4	14.4	16.0	70	1.5
	C	16.8	19.1									
20	B	19.6	20.4	60	225	15	55	12.3	15.6	18.0	60	1.5
	C	18.8	21.2									
22	B	21.6	22.4	60	250	20	55	14.1	17.6	20.0	60	1.25
	C	20.8	23.3									
24	B	23.5	24.5	60	250	25	70	15.9	19.6	22.0	55	1.25
	C	22.8	25.6									

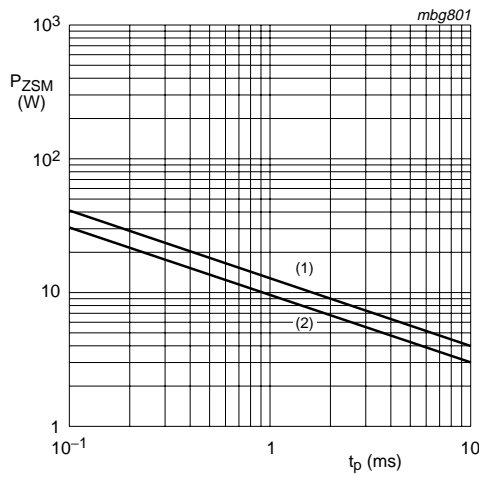
[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$ [2] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge

Table 9. Characteristics per type; BZV55-B27 to BZV55-C75

 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

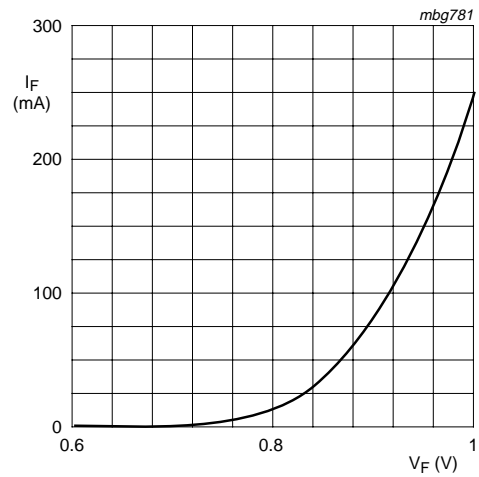
BZV55-xx	Sel	Working voltage V_Z (V)		Differential resistance r_{dif} (Ω)				Temperature coefficient S_Z (mV/K)			Diode capacitance C_d (pF) ^[1]	Non-repetitive peak reverse current I_{ZSM} (A) ^[2]
				$I_Z = 0.5\text{ mA}$		$I_Z = 2\text{ mA}$		$I_Z = 2\text{ mA}$				
		Min	Max	Typ	Max	Typ	Max	Min	Typ	Max	Max	Max
27	B	26.5	27.5	65	300	25	80	18.0	22.7	25.3	50	1.0
	C	25.1	28.9									
30	B	29.4	30.6	70	300	30	80	20.6	25.7	29.4	50	1.0
	C	28.0	32.0									
33	B	32.3	33.7	75	325	35	80	23.3	28.7	33.4	45	0.9
	C	31.0	35.0									
36	B	35.3	36.7	80	350	35	90	26.0	31.8	37.4	45	0.8
	C	34.0	38.0									
39	B	38.2	39.8	80	350	40	130	28.7	34.8	41.2	45	0.7
	C	37.0	41.0									
43	B	42.1	43.9	85	375	45	150	31.4	38.8	46.6	40	0.6
	C	40.0	46.0									
47	B	46.1	47.9	85	375	50	170	35.0	42.9	51.8	40	0.5
	C	44.0	50.0									
51	B	50.0	52.0	90	400	60	180	38.6	46.9	57.2	40	0.4
	C	48.0	54.0									
56	B	54.9	57.1	100	425	70	200	42.2	52.0	63.8	40	0.3
	C	52.0	60.0									
62	B	60.8	63.2	120	450	80	215	58.8	64.4	71.6	35	0.3
	C	58.0	66.0									
68	B	66.6	69.4	150	475	90	240	65.6	71.7	79.8	35	0.25
	C	64.0	72.0									
75	B	73.5	76.5	170	500	95	255	73.4	80.2	88.6	35	0.2
	C	70.0	79.0									

[1] $f = 1\text{ MHz}$; $V_R = 0\text{ V}$ [2] $t_p = 100\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge



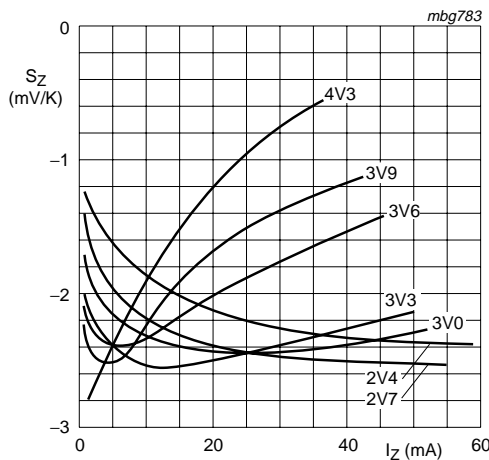
- (1) $T_j = 25\text{ °C}$ (prior to surge)
- (2) $T_j = 150\text{ °C}$ (prior to surge)

Fig 2. Non-repetitive peak reverse power dissipation as a function of pulse duration; maximum values



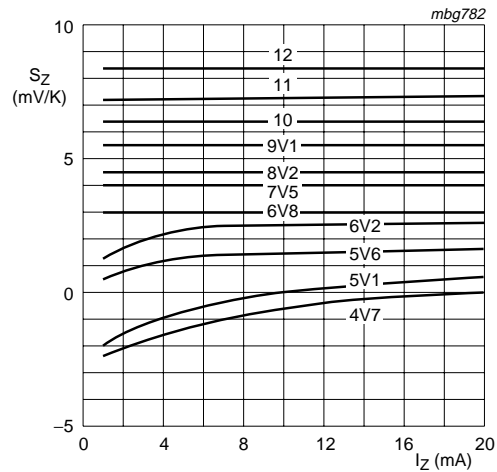
$T_j = 25\text{ °C}$

Fig 3. Forward current as a function of forward voltage; typical values



BZV55-B/C2V4 to BZV55-B/C4V3
 $T_j = 25\text{ °C}$ to 150 °C

Fig 4. Temperature coefficient as a function of working current; typical values



BZV55-B/C4V7 to BZV55-B/C12
 $T_j = 25\text{ °C}$ to 150 °C

Fig 5. Temperature coefficient as a function of working current; typical values

8. Package outline

Hermetically sealed glass surface-mounted package; 2 connectors

SOD80C

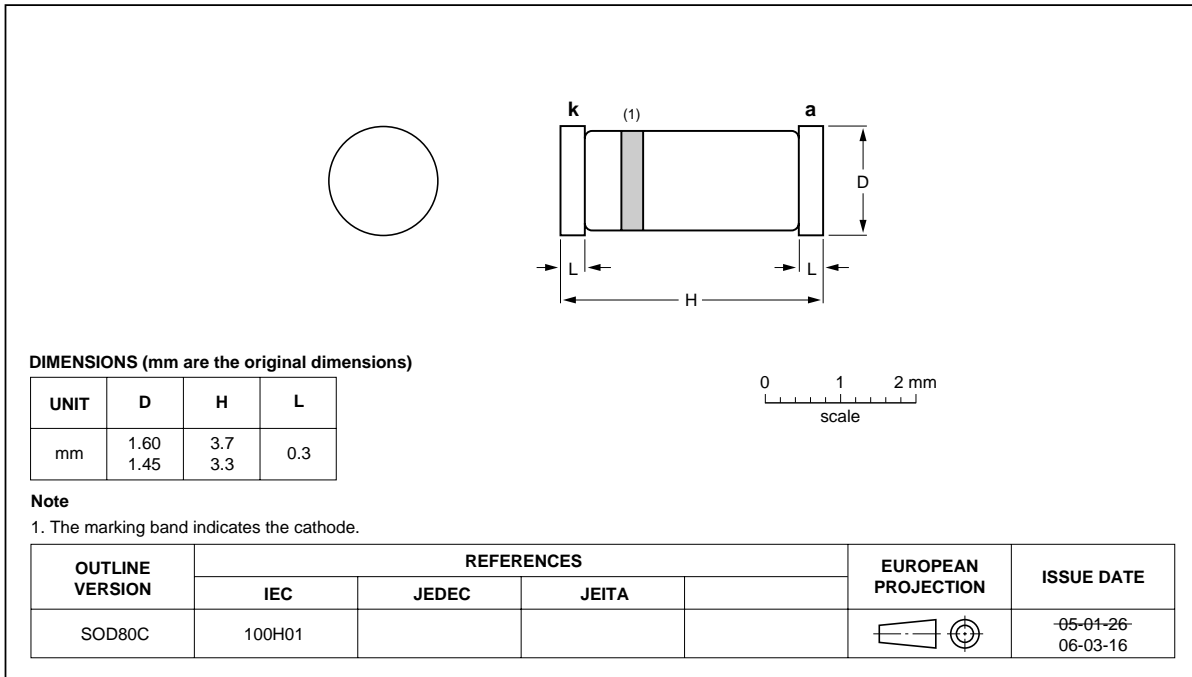


Fig 6. Package outline SOD80C

9. Packing information

Table 10. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			2500	10000
BZV55-B2V4 to BZV55-C75	SOD80C	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 13](#).

10. Soldering

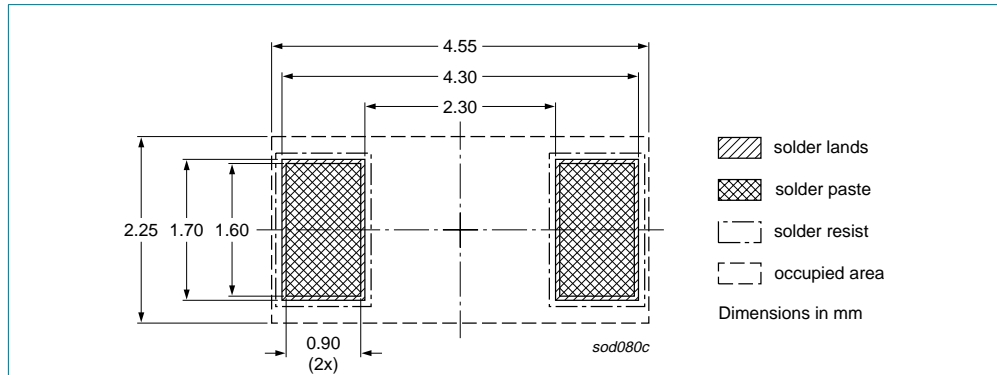


Fig 7. Reflow soldering footprint SOD80C

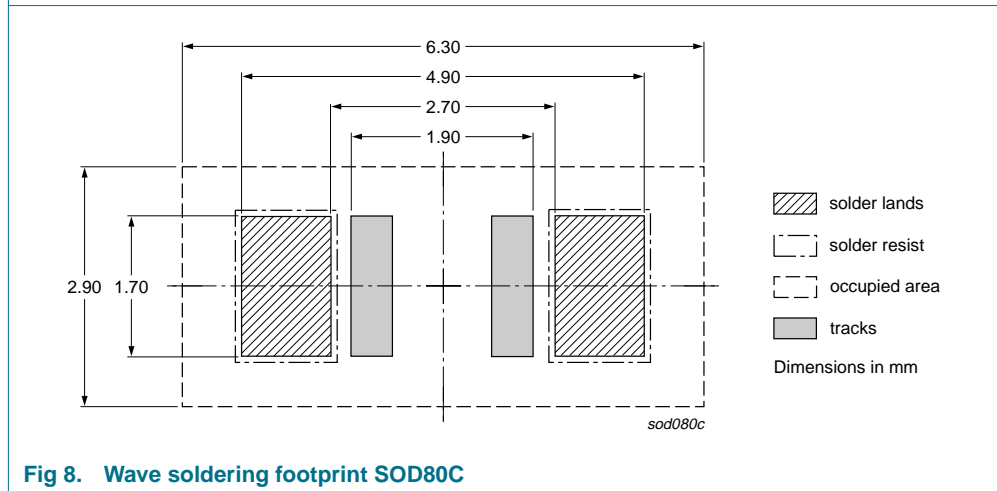


Fig 8. Wave soldering footprint SOD80C

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BZV55_SER_4	20070719	Product data sheet	CPCN200508022F	BZV55_3
Modifications:		<ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 4 "Marking": enhanced as per CPCN200508022F • Table 5: I_F continuous forward current redefined to forward current • Table 6: $R_{th(j-tp)}$ thermal resistance from junction to tie-point redefined to $R_{th(j-t)}$ • Figure 1: amended • Section 9 "Packing information": added • Section 12 "Legal information": updated 		
BZV55_3	20020228	Product specification	-	BZV55_2
BZV55_2	19990521	Product specification	-	BZV55_1
BZV55_1	19960426	Product specification	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

12.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For additional information, please visit: <http://www.nxp.com>

For sales office addresses, send an email to: salesaddresses@nxp.com

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	1
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	2
7	Characteristics	3
8	Package outline	8
9	Packing information	8
10	Soldering	9
11	Revision history	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	11
13	Contact information	11
14	Contents	12



Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2007.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 19 July 2007

Document identifier: BZV55_SER_4